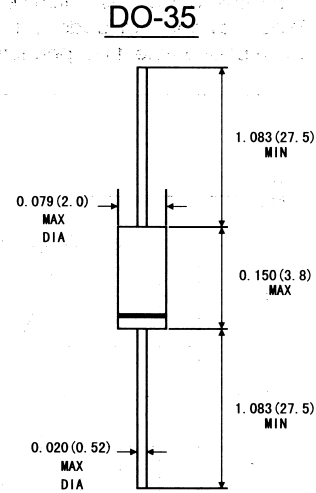


FEATURES

- The zener voltage are graded according to the international E24 standard .Other voltage tolerance and higher zener voltage on request.

MECHANICAL DATA

- Case:** DO-35 glass case
- Polarity:** Color band denotes cathode end
- Weight:** Approx. 0.13gram



Dimensions in inches and (millimeters)

ABSOLUTE MAXIMUM RATINGS(LIMITING VALUES)(TA=25°C)

	Symbols	Value	Units
Zener current see table "Characteristics"			
Power dissipation at TA=50°C	P _{tot}	500 ¹⁾	mW
Junction temperature	T _J	175	°C
Storage temperature range	T _{STG}	-65 to + 175	°C

1)Valid provided that at a distance of 8mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS(TA=25°C)

	Symbols	Min.	Typ.	Max.	Units
Thermal resistance junction to ambient	R _{θJA}			300 ¹⁾	K/W
Forward voltage at I _F =100mA	V _F			1	V

1)Valid provided that leads at a distance of 8mm from case are kept at ambient temperature



BXZ55... SILICON PLANAR ZENER DIODES

Type	Zener Voltage Range ¹⁾			Dynamic resistance			Reverse leakage current			Temp coefficient of zener voltage	
	V _{ZNOM}	I _{ZT} for V _{ZT} 2)		r _{zjt} and r _{zjk} at I _{zk}			I _R and I _{R2} at V _R			TK _{VZ}	
	V	mA	V	Ω	Ω	mA	μA	μA	V	%/K	
BZX 55/C 0V8 3)	0.8		0.73.0.83	<8	<50		-	-	-	-0.26...-0.23	
BZX 55/C 2V0	2.0		1.9.2.1	<85	<600	1	<100	<200	<1	-0.09...-0.06	
BZX 55/C 2V4	2.4		2.28.2.56				<50	<100			
BZX 55/C 2V7	2.7		2.5.2.9				<10	<50			
BZX 55/C 3V0	3		2.8.3.2				<4	<40			
BZX 55/C 3V3	3.3		3.1.3.5				<2				
BZX 55/C 3V6	3.6		3.4.3.8				<1	<20			-0.08...-0.05
BZX 55/C 3V9	3.9		3.7.4.1				<0.5	<10			
BZX 55/C 4V3	4.3		4.0.4.6				<75				-0.06...-0.03
BZX 55/C 4V7	4.7		4.4.5.0				<60				-0.05...+0.02
BZX 55/C 5V1	5.1		4.8.5.4				<35	<550			
BZX 55/C 5V6	5.6	5	5.2.6.0	<25	<450		-0.05...+0.05				
BZX 55/C 6V2	6.2		5.8.6.6	<10	<200	2.0	0.03.0.06				
BZX 55/C 6V8	6.8		6.4.7.2	<8	<150	3.0	0.03.0.07				
BZX 55/C 7V5	7.5		7.0.7.9	<7	<50	5.0	0.03.0.07				
BZX 55/C 8V2	8.2		7.7.8.7	<7		6.2	0.03.0.08				
BZX 55/C 9V1	9.1		8.5.9.6	<10		6.8	0.03.0.09				
BZX 55/C 10	10		9.4.10.6	<15	<70	<0.1	<2	7.5	0.03.0.1		
BZX 55/C 11	11		10.4.11.6	<20	<70			8.2	0.03.0.11		
BZX 55/C 12	12		11.4.12.7	<20	<90			9.1			
BZX 55/C 13	13		12.4.14.1	<26	<110			10.0			
BZX 55/C 15	15	13.8.15.6	<30	<110			11.0				
BZX 55/C 16	16	15.3.17.1	<40	<170			12				
BZX 55/C 18	18	16.8.19.1	<50	<170			13				
BZX 55/C 20	20	18.8.21.2	<55	<220			15				



BZX55... SILICON PLANAR ZENER DIODES

BZX 55/C 22	22	5	20.8.23.3	<55	<220	1	<2	16	0.04.0.12
BZX 55/C 24	24		22.8.25.6	<80				18	
BZX 55/C 27	27		25.1.28.9	<80				20	
BZX 55/C 30	30		28.32					22	
BZX 55/C 33	33		31.35					24	
BZX 55/C 36	36		34.38					27	
BZX 55/C 39	39	2.5	37.41	<500	0.5	<0.1	<5	30	
BZX 55/C 43	43		40.46	<500			33		
BZX 55/C 47	47		44.50	<600			36		
BZX 55/C 51	51		48.54	<700			39		
BZX 55/C 56	56		52.60	<700			43		
BZX 55/C 62	62		58.66	<1000			47		
BZX 55/C 68	68		64.72				51		
BZX 55/C 75	75		70.79				56		
BZX 55/C 82	82		77.87				<1500	62	
BZX 55/C 91	91		1	85.96			<2000	0.1	
BZX 55/C 100	100	94.106		<5000	75				
BZX 55/C 110	110	104.116		<5000	82				
BZX 55/C 120	120	114.127		<5500	91				
BZX 55/C 130	130	124.141		<6000	100				
BZX 55/C 150	150	138.156		<6500	110				
BZX 55/C 160	160	153.171		<7000	120				
BZX 55/C 180	180	168.191		<8500	130				
BZX 55/C 200	200	188.212		<10000	150				

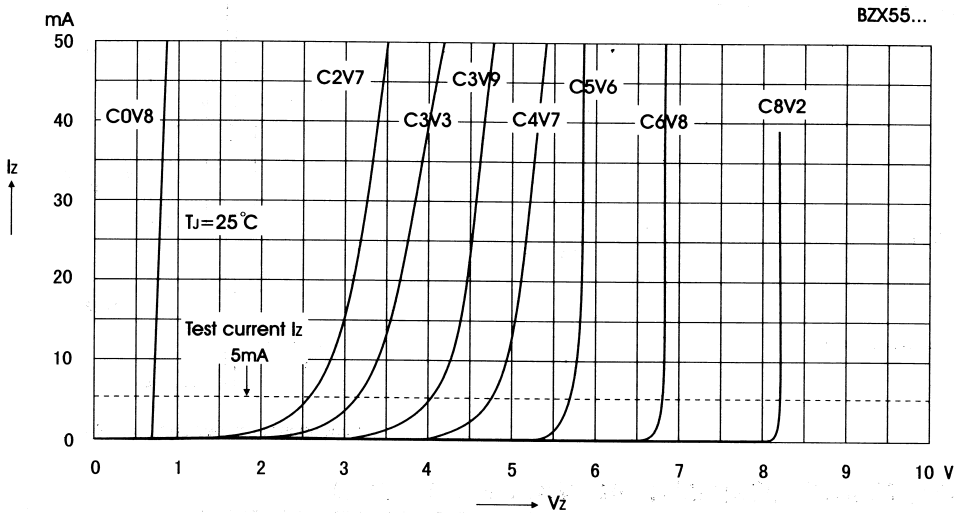
1) Tested with pulses $t_p=20\text{ms}$

2) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case

3) The BZX55-C0V8 is silicon diode with operation in forward direction. Hence, the index of all parameters should be 'F' instead of 'Z'. Connect the cathode lead to the negative pole.

BXZ55... SILICON PLANAR ZENER DIODES

BREAKDOWN CHARACTERISTICS AT T_J=CONSTANT(PULSED)



BREAKDOWN CHARACTERISTICS AT T_J=CONSTANT(PULSED)

